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Electronic Supplementary Information for:

An 8.7% efficiency co-electrodeposited Cu_2ZnSnS_4 photovoltaic device fabricated via a pressurized post-sulfurization process

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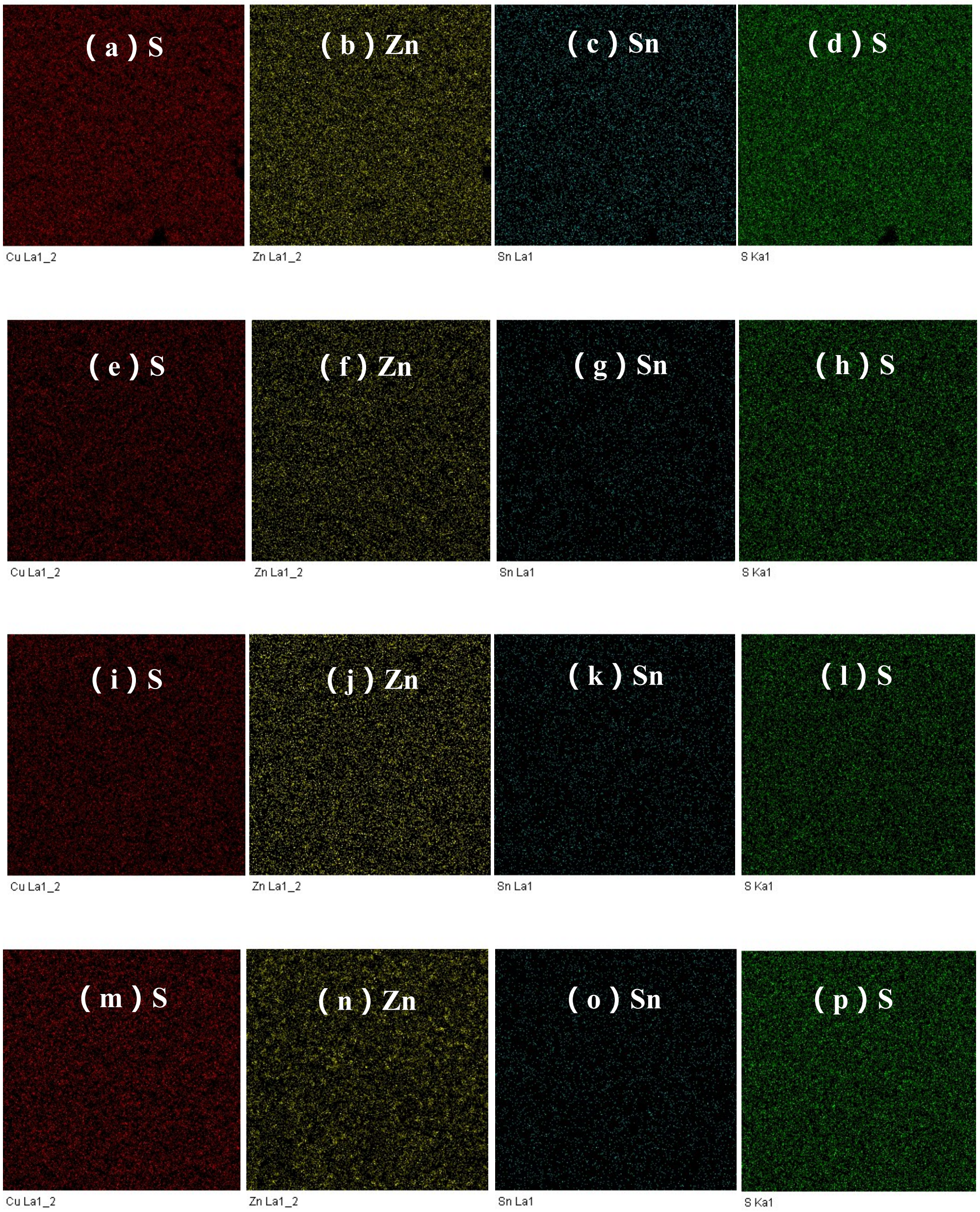

Fig. S1. The surface EDS mappings of CZTS films sulfurized at process pressure of 10 Torr (a, b, c, d), 20 Torr (e, f, g, h), 40 Torr (i, j, k, l) and 60 Torr (m, n, o, p).

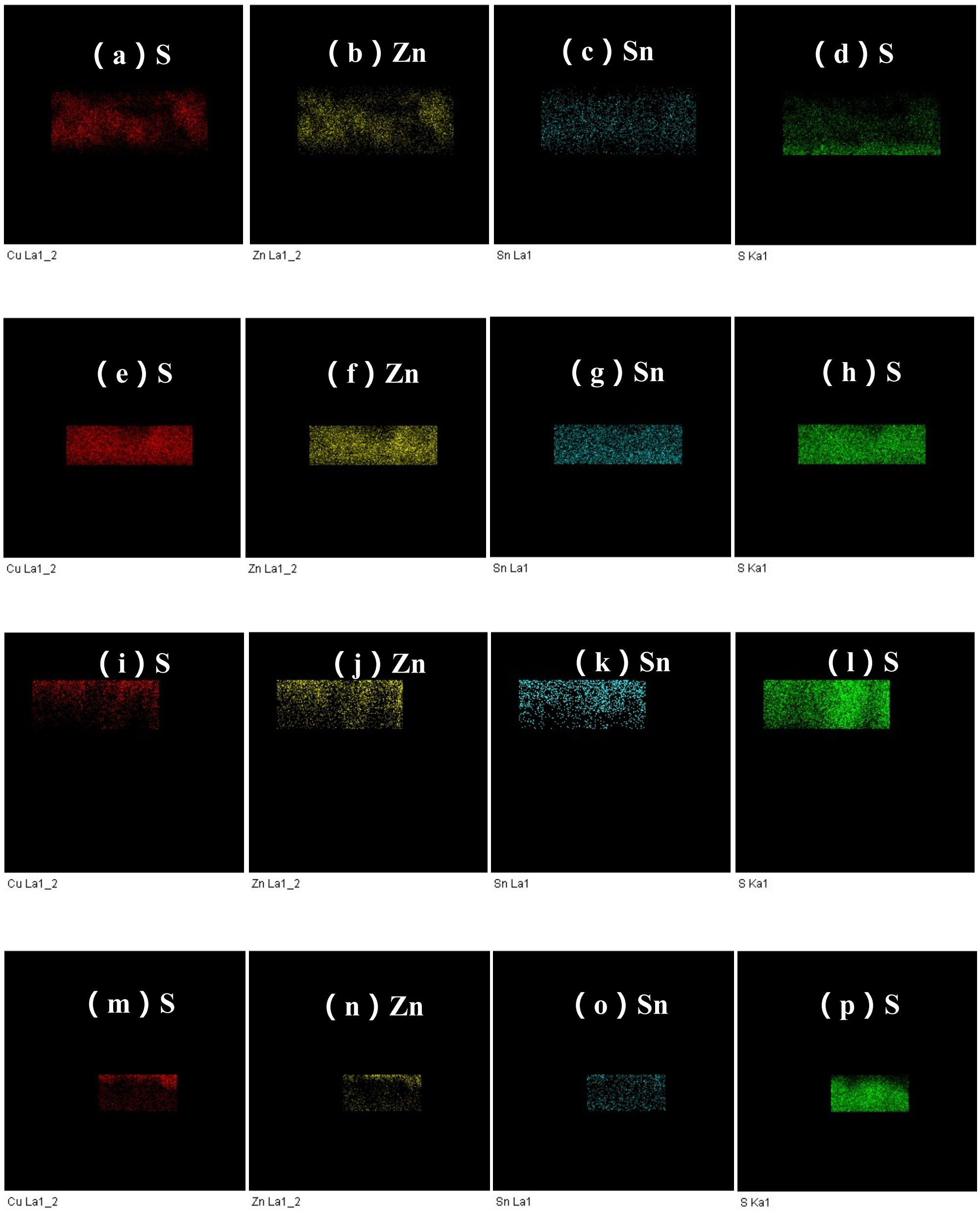

Fig. S2. The cross-sectional EDS mappings of CZTS films sulfurized at process pressure of 10 Torr (a, b, c, d), 20 Torr (e, f, g, h), 40 Torr (i, j, k, l), and 60 Torr (m, n, o, p).